

# Holger Bartolf

## List of Publications by Year in descending order

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32  
papers

483  
citations

1162889

8  
h-index

713332

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32  
all docs

32  
docs citations

32  
times ranked

636  
citing authors

#	ARTICLE	IF	CITATIONS
1	Optical and transport properties of ultrathin NbN films and nanostructures. Physical Review B, 2009, 80, .	1.1	148
2	Current-assisted thermally activated flux liberation in ultrathin nanopatterned NbN superconducting meander structures. Physical Review B, 2010, 81, .	1.1	122
3	Ultra-thin NbN films on Si: crystalline and superconducting properties. Journal of Physics: Conference Series, 2008, 97, 012045.	0.3	24
4	Development of a 60 $\mu\text{m}$ Deep Trench and Refill Process for Manufacturing Si-Based High-Voltage Super-Junction Structures. IEEE Transactions on Semiconductor Manufacturing, 2013, 26, 529-541.	1.4	23
5	Evidence for carbon clusters present near thermal gate oxides affecting the electronic band structure in SiC-MOSFET. Applied Physics Letters, 2019, 115, .	1.5	19
6	Current-Induced Critical State in NbN Thin-Film Structures. Journal of Low Temperature Physics, 2008, 151, 585-590.	0.6	17
7	Study of 4H-SiC Schottky Diode Designs for 3.3kV Applications. Materials Science Forum, 0, 778-780, 795-799.	0.3	17
8	Dopant imaging of power semiconductor device cross sections. Microelectronic Engineering, 2016, 160, 18-21.	1.1	11
9	Fluctuation Mechanisms in Superconductors. , 2016, , .		11
10	Temperature- and field-dependence of critical currents in NbN microbridges. Journal of Physics: Conference Series, 2008, 97, 012152.	0.3	10
11	Hall effect across the quantum phase transition of CeCuAu. Physica B: Condensed Matter, 2005, 359-361, 86-88.	1.3	8
12	A novel edge termination for high voltage SiC devices. , 2016, , .		8
13	Rare-earth intermetallic compounds at a magnetic instability. Journal of Alloys and Compounds, 2006, 408-412, 9-15.	2.8	6
14	Fabrication of metallic structures with lateral dimensions less than 15nm and $\langle \text{mml:math altimg="si6.gif" overflow="scroll" xmlns:xocs="http://www.elsevier.com/xml/xocs/dtd" xmlns:xs="http://www.w3.org/2001/XMLSchema" xmlns:xsi="http://www.w3.org/2001/XMLSchema-instance" xmlns="http://www.elsevier.com/xml/ja/dtd" xmlns:ja="http://www.elsevier.com/xml/ja/dtd" xmlns:mml="http://www.w3.org/1998/Math/MathML" xmlns:tb="http://www.elsevier.com/xml/common/table/dtd" \rangle$	0.6	6
15	Nanoscale fabrication by intrinsic suppression of proximity-electron exposures and general considerations for easy and effective top-down fabrication. Journal of Micromechanics and Microengineering, 2010, 20, 125015.	1.5	6
16	Large area scanning probe microscope in ultra-high vacuum demonstrated for electrostatic force measurements on high-voltage devices. Beilstein Journal of Nanotechnology, 2015, 6, 2485-2497.	1.5	6
17	Improving the Design of the Shield for the Electric Field in SiC-Based Schottky-Rectifiers and Ion-Implantation Cascades by SPM Dopant-Imaging. Microelectronic Engineering, 2015, 148, 1-4.	1.1	6
18	Optimization of 1700V 4H-SiC JBS Diode Parameters. Materials Science Forum, 0, 858, 782-785.	0.3	6

#	ARTICLE	IF	CITATIONS
19	Device Simulations on Novel High Channel Mobility 4H-SiC Trench MOSFETs and Their Fabrication Processes. <i>Microelectronic Engineering</i> , 2015, 145, 166-169.	1.1	4
20	Magnetotransport in. <i>Physica B: Condensed Matter</i> , 2006, 378-380, 44-45.	1.3	3
21	Inversion-Channel MOS Devices for Characterization of 4H-SiC/SiO <sub>2</sub> Interfaces. <i>Materials Science Forum</i> , 2015, 821-823, 480-483.	0.3	3
22	High Channel Mobility 4H-SiC MOSFETs by As and P Implantation Prior to Thermal Oxidation in N <sub>2</sub> O Atmosphere. <i>Materials Science Forum</i> , 2016, 858, 651-654.	0.3	3
23	Junction Barrier Schottky (JBS) Rectifier Interface Engineering Facilitated by Two-Dimensional (2D) Dopant Imaging. <i>Materials Science Forum</i> , 0, 858, 497-500.	0.3	3
24	Magnetic vortices in superconducting photon detectors. <i>Journal of Modern Optics</i> , 2009, 56, 352-357.	0.6	2
25	JBS power-rectifiers for 1.7kV applications with conduction properties close to pure Schottky-design. , 2015, , .		2
26	Two-Dimensional Carrier Profiling on Lightly Doped n-Type 4H-SiC Epitaxially Grown Layers. <i>Materials Science Forum</i> , 0, 821-823, 269-272.	0.3	2
27	Passivation of 4H-SiC/SiO <sub>2</sub> Interface Traps by Oxidation of a Thin Silicon Nitride Layer. <i>Materials Science Forum</i> , 2015, 821-823, 508-511.	0.3	2
28	Tailoring the 4H-SiC/SiO <sub>2</sub> MOS-interface for SiC-based power switches. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 08PC04.	0.8	2
29	NbN superconducting nanowire photon counters: magnetoconductivity and other detector properties. , 2009, , .		1
30	Comparison of the Planar-JBS against the Trench-MOS Rectifier-Design Based on 4H-SiC for 3.3 kV Applications. <i>Materials Science Forum</i> , 0, 821-823, 604-607.	0.3	1
31	On the Influence of Active Area Design on the Performance of SiC JBS Diodes. <i>Materials Science Forum</i> , 0, 897, 471-474.	0.3	1
32	Development of power semiconductors by quantitative nanoscale dopant imaging. , 2015, , .		0